

BoHS

COMPLIANT HALOGEN

FREE

Available

Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

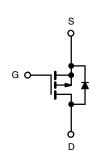
PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
- 20	0.015 at V _{GS} = - 4.5 V	- 13.2		
	0.020 at V _{GS} = - 2.5 V	- 11.4		
	0.029 at V _{GS} = - 1.8 V	- 9.5		

FEATURES

- Halogen-free According to IEC 61249-2-21 **Available**
- TrenchFET[®] Power MOSFET
- New PowerPAK[®] Package
- Low Thermal Resistance, RthJC - Low 1.07 mm Profile

APPLICATIONS

Load Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unles Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	– I _D	- 13.2	- 8.4		
	T _A = 85 °C		- 9.5	- 6.1		
Pulsed Drain Current		I _{DM}	- 30		A	
Continuous Source Current (Diode Conduction) ^a		I _S	- 3.2	- 1.3		
Maximum Power Dissipation ^a	T _A = 25 °C	– P _D	3.8	1.5	W	
	T _A = 85 °C		2.0	0.8		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{b, c}			260		Ĵ	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 s	- R _{thJA} R _{thJC}	26	33	
Maximum Junction-to-Ambient ^a	Steady State		65	81	°C/W
Maximum Junction-to-Case	Steady State		1.9	2.4	

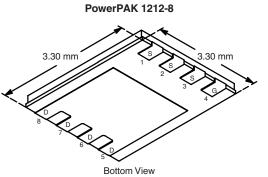
Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

Si7413DN-T1-GE3 (Lead (Pb)-free and Halogen-free)



Ordering Information: Si7413DN-T1-E3 (Lead (Pb)-free)

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Parameter	Symbol	Test Conditions	ons Min.		Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -400 \ \mu A$			- 1.0	V	
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V		± 100	nA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -20 V, V_{GS} = 0 V$			- 1		
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			- 5	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS}{\leq}$ - 5 V, V_{GS} = - 4.5 V	- 30			А	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 13.2 A		0.012	0.015	Ω	
		V _{GS} = - 2.5 V, I _D = - 11.4 A	0.016	0.020			
		V _{GS} = - 1.8 V, I _D = - 3.5 A		0.023	0.029		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 13.2 A		47		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 3.2 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			34	51		
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 13.2 A		5.4		nC	
Gate-Drain Charge	Q _{gd}			8.8			
Gate Resistance	R _g	f = 1 MHz		5		Ω	
Turn-On Delay Time	t _{d(on)}			30	45		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		50	75	ns	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_g = 6 Ω		200	300		
Fall Time	t _f			95	140		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 3.2 A, dl/dt = 100 A/μs		35	55		

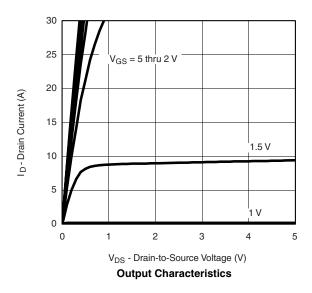
Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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Ciss

Coss

V_{DS} - Drain-to-Source Voltage (V)

Capacitance

8

12

16

20

Crss

4

V_{GS} = 4.5 V I_D = 13.2 A

- 25

 $I_{D} = 3.5 \text{ A}$

1

2

V_{GS} - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage

0

0

25

50

T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

I_D = 13.2 A

3

75

100

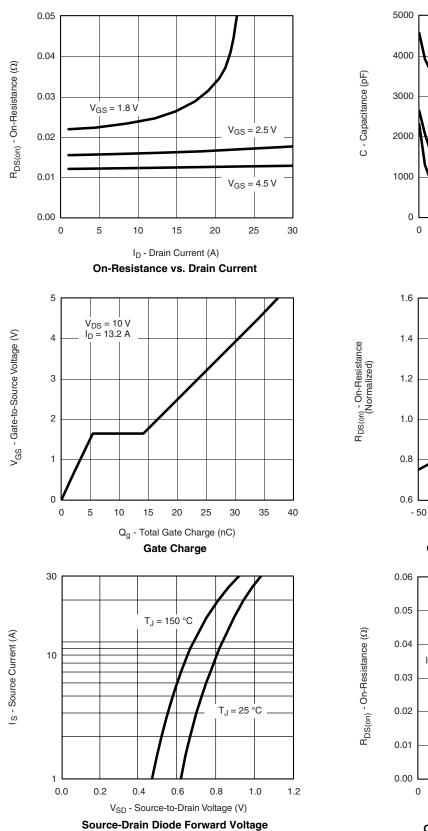
125

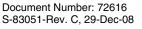
150

0

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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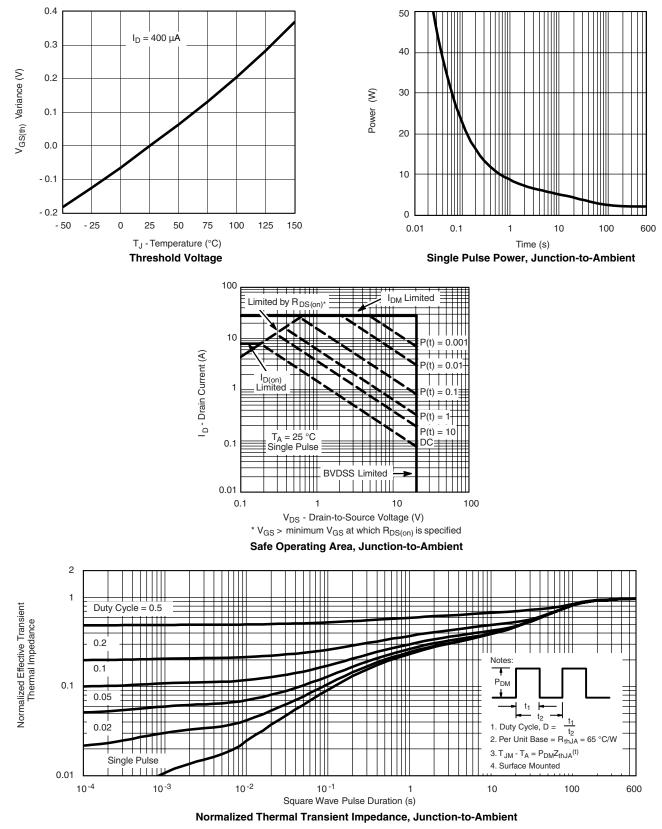
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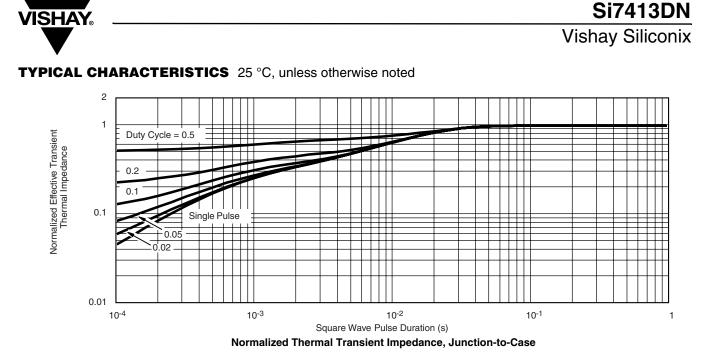
Si7413DN

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Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?72616</u>.



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